

MEMC 98-1451/2554.1
Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.

Serial No. To Be Assigned

Filed February 11, 2002

For THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL
SILICON

February 11, 2002

PRELIMINARY AMENDMENT A

TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

Please enter the following amendments.

IN THE TITLE:

Please replace the title with the following new title: "THERMAL ANNEALING
PROCESS FOR PRODUCING LOW DEFECT DENSITY SINGLE CRYSTAL SILICON."

IN THE SPECIFICATION:

Please replace the paragraph beginning at line 3, page 1 with the following
rewritten paragraph:

CROSS-REFERENCE TO RELATED APPLICATION

This patent application claims priority from U.S. Provisional Patent
Application Serial No. 60/104,304 filed on October 14, 1998, and U.S. Serial No.

09/416,998, filed on October 13, 1999, ~~now~~ now U.S. Patent # 6,416,836, issued

IN THE CLAIMS:

Please cancel claims 1-18.

7/09/2002.